	Type	L #	Hits	Search Text	DBs
1	BRS	L1	20272	buffer adj2 (layer or film or layers or films)	US-PGPUB; USPAT
2	BRS	L2	27959	high adj2 dielectric	US-PGPUB; USPAT
3	BRS	L3	0	1 near5 (ald near2 ((silicon adj dioxide) or "SiO.sub.2"))	US-PGPUB; USPAT
4	BRS	L4	2	1 near10 (ald near5 ((silicon adj dioxide) or "SiO.sub.2"))	US-PGPUB; USPAT
5	BRS	L5	1234	1 near5 ((silicon adj dioxide) or "SiO.sub.2")	US-PGPUB; USPAT
6	BRS	L6	5	2 near20 5	US-PGPUB; USPAT
7	BRS	L7	64	(ald near5 ((silicon adj dioxide) or "SiO.sub.2"))	US-PGPUB; USPAT
8	BRS	L8	232	7 near10 "9"(((silicon adj tetrachloride) or "SiCl.sub.4") near3 precursor)	US-PGPUB; USPAT
9	BRS	L9	0	7 near10 (((silicon adj tetrachloride) or "SiCl.sub.4") near3 precursor)	US-PGPUB; USPAT
10	BRS	L10	1	7 same (((silicon adj tetrachloride) or "SiCl.sub.4") near3 precursor)	US-PGPUB; USPAT
11	BRS	L11	232	(((silicon adj tetrachloride) or "SiCl.sub.4") near3 precursor)	US-PGPUB; USPAT

	Type	L #	Hits	Search Text	DBs
12	BRS	L12	39	11 near10 ((silicon adj dioxide) or "SiO.sub.2")	US-PGPUB; USPAT
13	BRS	L13	3	ald same (((silicon adj tetrachloride) or "SiCl.sub.4") near3 precursor)	US-PGPUB; USPAT
14	BRS	L14	4	(ald or (atomic adj layer adj deposition)) same (((silicon adj tetrachloride) or "SiCl.sub.4") near5 precursor)	US-PGPUB; USPAT
15	BRS	L15	1	14 not 13	US-PGPUB; USPAT
16	BRS	L16	0	(ald or (atomic adj layer adj deposition)) same (((silicon adj tetrachloride) or "SiCl.sub.4") near5 precursor)	USOCR; EPO; JPO; DERWENT; IBM_TDB
17	BRS	L17	0	(ald or (atomic adj layer adj deposition)) and (((silicon adj tetrachloride) or "SiCl.sub.4") near5 precursor)	USOCR; EPO; JPO; DERWENT; IBM_TDB
18	BRS	L18	28	(ald or (atomic adj layer adj deposition)) and (((silicon adj tetrachloride) or "SiCl.sub.4") near5 precursor)	US-PGPUB; USPAT